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Outstanding Combination of dc Precision and AC Performance:

Unity-Gain Bandwidth . . . 15 MHz Typ V_n 3.3 nV/ $\sqrt{\text{Hz}}$ at f = 10 Hz Typ,

2.5 nV/ $\sqrt{\text{Hz}}$ at f = 10 Hz Typ,

 V_{IO} 25 μ V Max

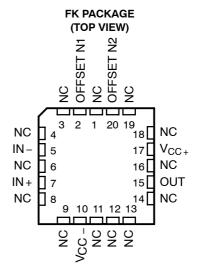
 $A_{VD} 45 V/μV Typ With R_L = 2 kΩ,$ 19 V/μV Typ With R_L = 600 Ω

- Available in Standard-Pinout Small-Outline Package
- Output Features Saturation Recovery Circuitry
- Macromodels and Statistical information

description

The TLE20x7 and TLE20x7A contain innovative circuit design expertise and high-quality process control techniques to produce a level of ac performance and dc precision previously unavailable in single operational amplifiers. Manufactured using Texas Instruments state-of-the-art Excalibur process, these devices allow upgrades to systems that use lower-precision devices.

In the area of dc precision, the TLE20x7 and TLE20x7A offer maximum offset voltages of 100 μ V and 25 μ V, respectively, common-mode rejection ratio of 131 dB (typ), supply voltage rejection ratio of 144 dB (typ), and dc gain of 45 V/ μ V (typ).



AVAILABLE OPTIONS

			PACKAGED	DEVICES		
T _A	V _{IO} max AT 25°C	SMALL OUTLINE [†] (D)	CHIP CARRIER (FK)	CERAMIC DIP (JG)	PLASTIC DIP (P)	CHIP FORM [‡] (Y)
0°C to 70°C	25 μV	TLE2027ACD TLE2037ACD	_ _		TLE2027ACP TLE2037ACP	TLE2027Y TLE2037Y
0°C to 70°C	100 μV	TLE2027CD TLE2037CD		_ _	TLE2027CP TLE2037CP	TLE2027Y TLE2037Y
-40°C to 105°C	25 μV	TLE2027AID TLE2037AID	_ _	_ _	TLE2027AIP TLE2037AIP	=
-40 C to 105 C	100 μV	TLE2027ID TLE2037ID		_	TLE2027IP TLE2037IP	_
-55°C to 125°C	25 μV	TLE2027AMD TLE2037AMD	TLE2027AMFK TLE2037AMFK	TLE2027AMJG TLE2037AMJG	TLE2027AMP TLE2037AMP	_
-55 0 10 125 0	100 μV	TLE2027MD TLE2037MD	TLE2027MFK TLE2037MFK	TLE2027MJG TLE2037MJG	TLE2027MP TLE2037MP	_

[†] The D packages are available taped and reeled. Add R suffix to device type (e.g., TLE2027ACDR).

[‡] Chip forms are tested at 25°C only.



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TEXAS INSTRUMENTS

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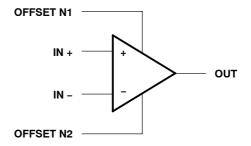
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description (continued)

The ac performance of the TLE2027 and TLE2037 is highlighted by a typical unity-gain bandwidth specification of 15 MHz, 55° of phase margin, and noise voltage specifications of 3.3 nV/ $\sqrt{\text{Hz}}$ and 2.5 nV/ $\sqrt{\text{Hz}}$ at frequencies of 10 Hz and 1 kHz respectively. The TLE2037 and TLE2037A have been decompensated for faster slew rate (-7.5 V/ μ s, typical) and wider bandwidth (50 MHz). To ensure stability, the TLE2037 and TLE2037A should be operated with a closed-loop gain of 5 or greater.

Both the TLE20x7 and TLE20x7A are available in a wide variety of packages, including the industry-standard 8-pin small-outline version for high-density system applications. The C-suffix devices are characterized for operation from 0°C to 70°C. The I-suffix devices are characterized for operation from -40°C to 105°C. The M-suffix devices are characterized for operation over the full military temperature range of -55°C to 125°C.

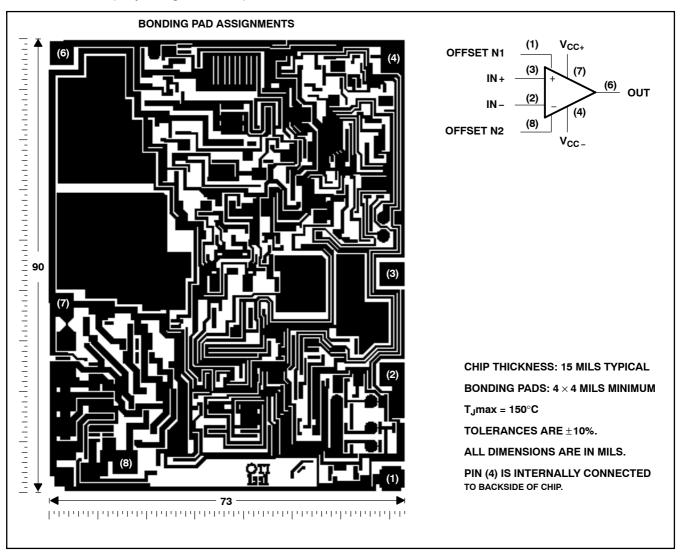
symbol



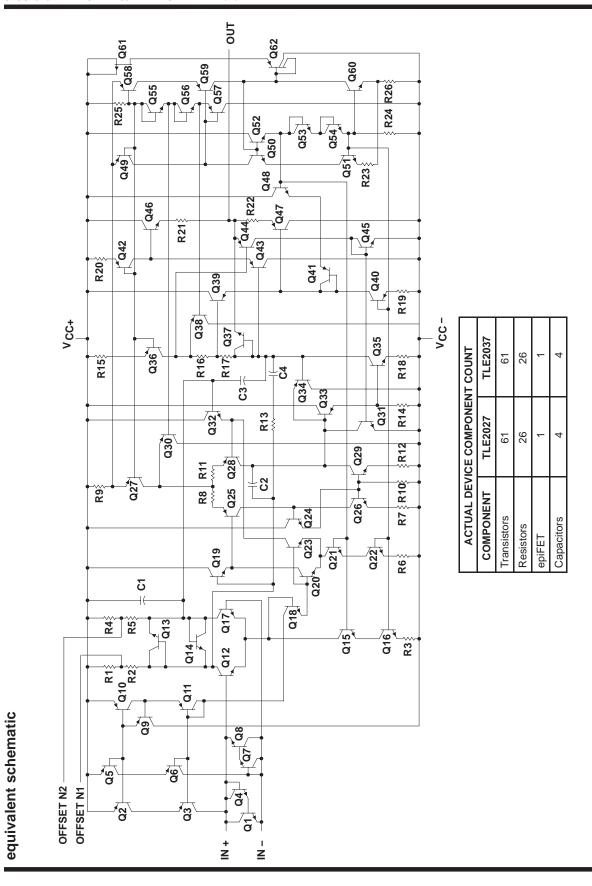
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TLE202xY chip information

This chip, when properly assembled, displays characteristics similar to the TLE202xC. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. The chip may be mounted with conductive epoxy or a gold-silicon preform.



TLE2027, TLE2037, TLE2027A, TLE2037A, TLE2027Y, TLE2037Y EXCALIBUR LOW-NOISE HIGH-SPEED PRECISION OPERATIONAL AMPLIFIERS SLOS192C - FEBRUARY 1997 - REVISED APRIL 2010



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absolute maximum ratings over operating free-air temperature range (unless otherwise noted) †

Supply voltage, V _{CC+} (see Note 1)	19 V
Supply voltage, V _{CC-}	– 19 V
Differential input voltage, V _{ID} (see Note 2)	
Input voltage range, V _I (any input)	V _{CC±}
Input current, I _I (each Input)	±1 mA
Output current, I _O	± 50 mA
Total current into V _{CC+}	50 mA
Total current out of V _{CC}	50 mA
Duration of short-circuit current at (or below) 25°C (see Note 3)	unlimited
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T _A : C suffix	0°C to 70°C
I suffix	– 40°C to 105°C
M suffix	– 55°C to 125°C
Storage temperature range, T _{stg}	– 65°C to 150°C
Case temperature for 60 seconds, T _C : FK package	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: [or P package 260°C
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds: J	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values, except differential voltages, are with respect to the midpoint between V_{CC +} and V_{CC -}.

- 2. Differential voltages are at IN+ with respect to IN –. Excessive current flows if a differential input voltage in excess of approximately ±1.2 V is applied between the inputs unless some limiting resistance is used.
- 3. The output may be shorted to either supply. Temperature and/or supply voltages must be limited to ensure that the maximum dissipation rating is not exceeded.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR ABOVE T _A = 25°C	T _A = 70°C POWER RATING	T _A = 105°C POWER RATING	T _A = 125°C POWER RATING
D	725 mW	5.8 mW/°C	464 mW	261 mW	145 mW
FK	1375 mW	11.0 mW/°C	880 mW	495 mW	275 mW
JG	1050 mW	8.4 mW/°C	672 mW	378 mW	210 mW
Р	1000 mW	8.0 mW/°C	640 mW	360 mW	200 mW

recommended operating conditions

		C SUF	FIX	I SUF	FIX	M SUI	FIX	LINUT
		MIN	MAX	MIN	MAX	MIN	MAX	UNIT
Supply voltage, V _{CC±}		±4	± 19	±4	±19	±4	±19	V
O management of the second	T _A = 25°C	- 11	11	-11	11	-11	11	
Common-mode input voltage, V _{IC}	T _A = Full range [‡]	-10.5	10.5	-10.4	10.4	-10.2	10.2	V
Operating free-air temperature, T _A		0	70	-40	105	-55	125	°C

[‡] Full range is 0°C to 70°C for C-suffix devices, -40°C to 105°C for I-suffix devices, and -55°C to 125°C for M-suffix devices.



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TLE20x7C electrical characteristics at specified free-air temperature, $V_{CC\pm}$ = ± 15 V (unless otherwise noted)

	DADAMETER	TECT COMPITIONS	_ +	Т	LE20x7	С	TI	E20x7A	С	
	PARAMETER	TEST CONDITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V	lanut offeet voltege		25°C		20	100		10	25	/
V_{IO}	Input offset voltage		Full range			145			70	μV
α_{VIO}	Temperature coefficient of input offset voltage		Full range		0.4	1		0.2	1	μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{IC} = 0$, $R_S = 50 \Omega$	25°C		0.006	1		0.006	1	μV/mo
	Input offset surrent		25°C		6	90		6	90	nA
I _{IO}	Input offset current		Full range			150			150	IIA
1	Input bias current		25°C		15	90		15	90	nA
I _{IB}	input bias current		Full range			150			150	ПА
V	Common-mode input	D 500	25°C	-11 to 11	-13 to 13		–11 to 11	–13 to 13		.,
V _{ICR}	voltage range	R _S = 50 Ω	Full range	-10.5 to 10.5			-10.5 to 10.5			V
		D 200 C	25°C	10.5	12.9		10.5	12.9		
	Maximum positive peak	$R_L = 600 \Omega$	Full range	10			10			١.,
V _{OM} +	output voltage swing	B 010	25°C	12	13.2		12	13.2		V
		$R_L = 2 k\Omega$	Full range	11			11			
		D 000 0	25°C	-10.5	-13		-10.5	-13		
V	Maximum negative peak	R _L = 600 Ω	Full range	-10			-10			V
V _{OM} -	output voltage swing	D Also	25°C	- 12	-13.5		- 12	-13.5		V
		$R_L = 2 k\Omega$	Full range	- 11			- 11			
		$V_O = \pm 11 \ V$, $R_L = 2 \ k\Omega$	25°C	5	45		10	45		
		$V_O = \pm 10 \text{ V}, R_L = 2 \text{ k}\Omega$	Full range	2			4			
	Large-signal differential	V .40V B 410	25°C	3.5	38		8	38] ,,, ,,
A_{VD}	voltage amplification	$V_O = \pm 10 \text{ V}, R_L = 1 \text{ k}\Omega$	Full range	1			2.5			V/μV
		$V_0 = \pm 10 \text{ V},$	25°C	2	19		5	19		
		$R_L = 600 \Omega$	Full range	0.5			2			
C _i	Input capacitance		25°C		8			8		pF
z _o	Open-loop output impedance	I _O = 0	25°C		50			50		Ω
OL LIDE	Common-mode rejection	V _{IC} = V _{ICR} min,	25°C	100	131		117	131		
CMRR	ratio	$R_S = 50 \Omega$	Full range	98			114			dB
le	Supply-voltage rejection	$V_{CC\pm} = \pm 4 \text{ V to } \pm 18 \text{ V},$ $R_S = 50 \Omega$	25°C	94	144		110	144		dВ
k _{SVR}	ratio ($\Delta V_{CC\pm} / \Delta V_{IO}$)	$V_{CC\pm}$ = ±4 V to ±18 V, R _S = 50 Ω	Full range	92			106			dB
	Cumply augrant	V O Notest	25°C		3.8	5.3		3.8	5.3	A
I _{CC}	Supply current	$V_O = 0$, No load	Full range		·	5.6		· · · · · · · · · · · · · · · · · · ·	5.6	mA

[†] Full range is 0°C to 70°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^{\circ}C$ extrapolated to $T_A = 25^{\circ}C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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TLE20x7C operating characteristics at specified free-air temperature, $V_{CC\,\pm}$ = ± 15 V, T_A = 25°C (unless otherwise specified)

	DADAMETED	TEGT 001101	-		TLE20x7C		1	ΓLE20x7AC		
	PARAMETER	TEST CONDI	IIONS	MIN	TYP	MAX	MIN	1.7 2.8 6 7.5 1.2 5 3.3 4.5 2.5 3.8 50 130 10 25 0.8 1.8 <0.002% <0.002% <0.002% 9(6) 13 35 50 30 80 80 55°	UNIT	
		$R_L = 2 k\Omega$, $C_L = 100 pF$,	TLE2027	1.7	2.8		1.7	2.8		
		See Figure 1	TLE2037	6	7.5		6	7.5		
SR	Slew rate at unity gain	$R_L = 2 k\Omega$, $C_L = 100 pF$,	TLE2027	1.2			1.2			V/μs
		$T_A = 0$ °C to 70°C, See Figure 1	TLE2037	5			5			
.,	Equivalent input noise volt-	$R_S = 20 \Omega$,	f = 10 Hz		3.3	8		3.3	4.5	~\// ₀ / -
V _n	age (see Figure 2)	$R_S = 20 \Omega$,	f = 1 kHz		2.5	4.5		2.5	3.8	nV/√ Hz
V _{N(PP)}	Peak-to-peak equivalent in- put noise voltage	f = 0.1 Hz to 10 Hz			50	250		50	130	nV
	Equivalent input noise cur-	f = 10 Hz			10	25		10	25	- A / / III
In	rent	f = 1 kHz			0.8	1.8		0.8	1.8	pA/√ Hz
T. 16	Table on the date of the	V _O = +10 V, A _{VD} = 1, See Note 5	TLE2027		<0.002%			<0.002%		
THD	Total harmonic distortion	$V_O = +10 \text{ V},$ $A_{VD} = 5,$ See Note 5	TLE2037		<0.002%			<0.002%		
B ₁	Unity-gain bandwidth (see Figure 3)	$R_L = 2 k\Omega$, $C_L = 100 pF$	TLE2027	9(6)	13		9(6)	13		
GBW	Gain bandwidth product	$R_L = 2 k\Omega$, $C_L = 100 pF$	TLE2037	35	50		35	50		MHz
Б	Maximum output-swing	D 010	TLE2027		30			30		
B _{OM}	bandwidth	$R_L = 2 k\Omega$	TLE2037		80			80		kHz
Α	Phase margin at unity gain	$R_L = 2 k\Omega$,	TLE2027		55°			55°		
Φm	(see Figure 3)	C _L = 100 pF	TLE2037		50°			50°		

NOTE 5: Measured distortion of the source used in the analysis was 0.002%.

NOTE 6: This parameter is not production tested



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TLE20x7l electrical characteristics at specified free-air temperature, V_{CC^\pm} = ± 15 V (unless otherwise noted)

				T	LE20x7		TI	E20x7A	I	
	PARAMETER	TEST CONDITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V	land offeet veltage		25°C		20	100		10	25	
V_{IO}	Input offset voltage		Full range			180			105	μV
α_{VIO}	Temperature coefficient of input offset voltage		Full range		0.4	1		0.2	1	μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{IC} = 0$, $R_S = 50 \Omega$	25°C		0.006	1		0.006	1	μV/mo
	land effect ourrent		25°C		6	90		6	90	~^
I _{IO}	Input offset current		Full range			150			150	nA
	Input bias current		25°C		15	90		15	90	nA
I _{IB}	input bias current		Full range			150			150	ПА
	Common-mode input	D 500	25°C	–11 to 11	-13 to 13		-11 to 11	-13 to 13		V
V _{ICR}	voltage range	$R_S = 50 \Omega$	Full range	-10.4 to 10.4			-10.4 to 10.4			V
		D 000 O	25°C	10.5	12.9		10.5	12.9		
l.,	Maximum positive peak	$R_L = 600 \Omega$	Full range	10			10			.,
V _{OM +}	output voltage swing	D ALO	25°C	12	13.2		12	13.2		V
		$R_L = 2 k\Omega$	Full range	11			11			
		P 600 O	25°C	-10.5	-13		-10.5	-13		
V	Maximum negative peak	R _L = 600 Ω	Full range	-10			-10			V
V _{OM} -	output voltage swing	$R_L = 2 k\Omega$	25°C	- 12	- 13.5		- 12	- 13.5		V
		⊓[= 2 ks2	Full range	- 11			- 11			
		$V_O = \pm 11 \text{ V}, R_L = 2 \text{ k}\Omega$	25°C	5	45		10	45		
		$V_O = \pm 10 \text{ V}, \ R_L = 2 \text{ k}\Omega$	Full range	2			3.5			
١,	Large-signal differential	V 140 V D 4 k0	25°C	3.5	38		8	38		1//1
A_{VD}	voltage amplification	$V_O = \pm 10 \text{ V}, R_L = 1 \text{ k}\Omega$	Full range	1			2.2			V/µV
		V 140 V D 600 O	25°C	2	19		5	19		
		$V_O = \pm 10 \text{ V}, \ R_L = 600 \ \Omega$	Full range	0.5			1.1			
Ci	Input capacitance		25°C		8			8		pF
z _o	Open-loop output impedance	I _O = 0	25°C		50			50		Ω
OMBB	Common-mode rejection	V _{IC} = V _{ICR} min,	25°C	100	131		117	131		40
CMRR	ratio	$R_S = 50 \Omega$	Full range	96			113			dB
b	Supply-voltage rejection	$V_{CC\pm} = \pm 4 \text{ V to } \pm 18 \text{ V},$ $R_S = 50 \Omega$	25°C	94	144		110	144		4D
	ratio ($\Delta V_{CC\pm}/\Delta V_{IO}$) $V_{CC\pm}$	$V_{CC\pm}$ = ±4 V to ±18 V, R _S = 50 Ω	Full range	90			105			dB
loo	Supply current	Vo = 0 No load	25°C		3.8	5.3		3.8	5.3	mA
Icc	очрріў синені	$V_{\odot} = 0$. No load	Full range			5.6			5.6	111/4

[†] Full range is – 40°C to 105°C.



NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^{\circ}C$ extrapolated to $T_A = 25^{\circ}C$ using the Arrhenius equation and assuming an activation energy of 0.96 eV.

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TLE20x7l operating characteristics at specified free-air temperature, $V_{CC\,\pm}$ = ± 15 V, T_A = 25°C (unless otherwise specified)

	24244555	TEST SOURIE			TLE20x7l		7	ΓLE20x7AI		
	PARAMETER	TEST CONDIT	IONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
		$R_L = 2 k\Omega$,	TLE2027	1.7	2.8		1.7	2.8		
		C _L = 100 pF, See Figure 1	TLE2037	6	7.5		6	7.5		
SR	Slew rate at unity gain	$R_L = 2 k\Omega$, $C_L = 100 pF$,	TLE2027	1.1			1.1			V/μs
		$T_A = -40^{\circ}C$ to $85^{\circ}C$, See Figure 1	TLE2037	4.7			4.7			
.,	Equivalent input noise	$R_S = 20 \Omega$,	f = 10 Hz		3.3	8		3.3	4.5	nV/√ Hz
V _n	voltage (see Figure 2)	$R_S = 20 \Omega$,	f = 1 kHz		2.5	4.5		2.5	3.8	IIV/∀⊓Z
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz			50	250		50	130	nV
	Equivalent input noise	f = 10 Hz			10	25		10	25	/
I _n	current	f = 1 kHz			0.8	1,8		0.8	1.8	pA/√ Hz
T. 16	-	V _O = +10 V, A _{VD} = 1, See Note 5	TLE2027		< 0.002%			< 0.002%		
THD	Total harmonic distortion	V _O = +10 V, A _{VD} = 5, See Note 5	TLE2037		< 0.002%			< 0.002%		
B ₁	Unity-gain bandwidth (see Figure 3)	$R_L = 2 k\Omega$, $C_L = 100 pF$	TLE2027	9(6)	13		9(6)	13		
GBW	Gain bandwidth product	$R_L = 2 k\Omega$, $C_L = 100 pF$	TLE2037	35	50		35	50		MHz
	Maximum output-swing	D 010	TLE2027		30			30		
B _{OM}	bandwidth	$R_L = 2 k\Omega$	TLE2037		80			80		kHz
<u></u>	Phase margin at unity	$R_L = 2 k\Omega$,	TLE2027		55°			55°		
Φm	gain (see Figure 3)	C _L = 100 pF	TLE2037		50°		•	50°		

NOTE 5: Measured distortion of the source used in the analysis was 0.002%.

NOTE 6: This parameter is not production tested.



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TLE20x7M electrical characteristics at specified free-air temperature, $V_{CC\pm}$ = ± 15 V (unless otherwise noted)

				T	LE20x7N	1	TL	E20x7Al	М	
	PARAMETER	TEST CONDITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V	land offeet veltage		25°C		20	100		10	25	\/
V_{IO}	Input offset voltage		Full range			200			105	μV
α_{VIO}	Temperature coefficient of input offset voltage		Full range		0.4	1*		0.2	1*	μV/°C
	Input offset voltage long-term drift (see Note 4)	$V_{IC} = 0$, $R_S = 50 \Omega$	25°C		0.006	1*		0.006	1*	μV/mo
	land effect oursest		25°C		6	90		6	90	^
I _{IO}	Input offset current		Full range			150			150	nA
	land his a summer		25°C		15	90		15	90	A
I _{IB}	Input bias current		Full range			150			150	nA
V _{ICR}	Common-mode input	$R_S = 50 \Omega$	25°C	–11 to 11	-13 to 13		–11 to 11	-13 to 13		٧
VICR	R voltage range	11.5 - 00 12	Full range	-10.3 to 10.3			-10.4 to 10.4			•
		P 600 O	25°C	10.5	12.9		10.5	12.9		
V	Maximum positive peak	$R_L = 600 \Omega$	Full range	10			10			V
V _{OM +}	output voltage swing	P. 010	25°C	12	13.2		12	13.2		V
		$R_L = 2 k\Omega$	Full range	11			11			
		P 600 O	25°C -10.5 -13		-10.5	-13				
V	Maximum negative peak	$R_L = 600 \Omega$	Full range	-10			-10			V
V _{OM} -	output voltage swing	$R_L = 2 k\Omega$	25°C	- 12	-13.5		- 12	- 13.5		
		_	Full range	- 11			- 11			
		$V_O = \pm 11 \text{ V}, R_L = 2 \text{ k}\Omega$	25°C	5	45		10	45		
	Large-signal differential	$V_O = \pm 10 \text{ V}, R_L = 2 \text{ k}\Omega$	Full range	2.5			3.5			
A_{VD}	voltage amplification	$V_O = \pm 10 \text{ V}, R_L = 1 \text{ k}\Omega$	25°C	3.5	38		8	38		V/µV
	5 1	V() = ±10 V, T([= 1 K22	Full range	1.8			2.2			
		$V_O = \pm 10 \text{ V}, R_L = 600 \Omega$	25°C	2	19		5	19		
Ci	Input capacitance		25°C		8			8		pF
z _o	Open-loop output impedance	I _O = 0	25°C		50			50		Ω
CMDD	Common-mode rejection	V _{IC} = V _{ICR} min,	25°C	100	131		117	131		10
CMRR	ratio	$R_S = 50 \Omega$	Full range	96			113			dB
le	Supply-voltage rejection	$V_{CC\pm} = \pm 4 \text{ V to } \pm 18 \text{ V},$ $R_S = 50 \Omega$	25°C	94	144		110	144		dB
k _{SVR}	ratio ($\Delta V_{CC\pm} / \Delta V_{IO}$) $V_{CC\pm} / \Delta V_{IO}$	$V_{CC\pm}$ = ±4 V to ±18 V, R _S = 50 Ω	Full range	90			105			ub
loo	Supply current	V _O = 0, No load	25°C		3.8	5.3		3.8	5.3	mA
I _{CC}	очрріў сипопі	*0 - 0, 140 load	Full range			5.6			5.6	111/5

^{*} On products compliant to MIL-PRF-38535, this parameter is not production tested.



[†] Full range is – 55°C to 125°C.

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at T_A = 150°C extrapolated to T_A = 25°C using the Arrhenius equation and assuming an activation energy of 0.96 eV.

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TLE20x7M operating characteristics at specified free-air temperature, $V_{CC\,\pm}$ = ± 15 V, T_A = 25°C (unless otherwise specified)

	DADAMETED	TEGT COMPLET	ONO.		TLE20x7M		7	ΓLE20x7AM		
	PARAMETER	TEST CONDITI	ONS	MIN	TYP	MAX	MIN	1.7 2.8 6* 7.5 1 4.4* 3.3 8* 2.5 4* 225 375* 25 2.5 < 0.002% < 0.002% 9* 13 35 50		UNIT
		$R_L = 2 k\Omega$	TLE2027	1.7	2.8		1.7	2.8		
		C _L = 100 pF, See Figure 1	TLE2037	6*	7.5		6*	7.5		
SR	Slew rate at unity gain	$R_L = 2 k\Omega$, $C_L = 100 pF$,	TLE2027	1			1			V/μs
		$T_A = -55^{\circ}C$ to 125°C, See Figure 1	TLE2037	4.4*			4.4*			
V	Equivalent input noise	$R_S = 20 \Omega$,	f = 10 Hz		3.3	8*				->.///
V _n	voltage (see Figure 2)	$R_S = 20 \Omega$,	f = 1 kHz		2.5	4*		2.5	4*	nV/√ Hz
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz			225	375*		225	375*	nV
	Equivalent input noise	f = 10 Hz			25					A / /TT
I _n	current	f = 1 kHz			2.5			2.5		pA/√ Hz
T. 15	-	V _O = +10 V, A _{VD} = 1, See Note 5	TLE2027		< 0.002%			< 0.002%		
THD	Total harmonic distortion	V _O = +10 V, A _{VD} = 5, See Note 5	TLE2037		< 0.002%			< 0.002%		
_	Unity-gain bandwidth	$R_L = 2 k\Omega$,	TLE2027	7*	13		9*	13		NAL 1-
B ₁	(see Figure 3)	C _L = 100 pF	TLE2037	35	50		35	50		MHz
D	Maximum output-swing	B 2160	TLE2027		30		30		kHz	
B _{OM}	bandwidth	$R_L = 2 k\Omega$	TLE2037		80		80		KITZ	
_	Phase margin at unity	$R_L = 2 k\Omega$,	TLE2027		55°			55°		
Φm	gain (see Figure 3)	C _L = 100 pF	TLE2037		50°			50°		

^{*} On products compliant to MIL-PRF-38535, this parameter is not production tested.

NOTE 5: Measured distortion of the source used in the analysis was 0.002%.

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TLE20x7Y electrical characteristics, $V_{CC\pm}$ = ± 15 V, T_A = 25°C (unless otherwise noted)

	DADAMETED	TEGT COMPLETIONS	TI	_E20x7\	1	
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{IO}	Input offset voltage			20		μV
	Input offset voltage long-term drift (see Note 4)	$V_{IC} = 0$, $R_S = 50 \Omega$		0.006		μV/mo
I _{IO}	Input offset current	1		6		nA
I _{IB}	Input bias current			15		nA
V _{ICR}	Common-mode input voltage range	R _S = 50 Ω		-13 to 13		>
		$R_L = 600 \Omega$		12.9		
V _{OM +}	Maximum positive peak output voltage swing	$R_L = 2 k\Omega$		13.2		V
.,		$R_L = 600 \Omega$		-13		
V _{OM} -	Maximum negative peak output voltage swing	$R_L = 2 k\Omega$		-13.5		V
		$V_O = \pm 11 \ V$, $R_L = 2 \ k\Omega$		45		
A _{VD}	Large-signal differential voltage amplification	$V_O = \pm 10 \ V$, $R_L = 1 \ k\Omega$		38		V/µV
7.00	Edigo oighai amoroniai voitago ampimoation	$V_O = \pm 10 \text{ V},$ $R_L = 600 \Omega$		19		۷/μν
Ci	Input capacitance			8		pF
z _o	Open-loop output impedance	I _O = 0		50		Ω
CMRR	Common-mode rejection ratio	$V_{IC} = V_{ICR}min,$ $R_S = 50 \Omega$		131		dB
k _{SVR}	Supply-voltage rejection ratio ($\Delta V_{CC\pm}$ / $\Delta V_{IO)}$	$V_{CC\pm} = \pm 4 \text{ V to } \pm 18 \text{ V},$ $R_S = 50 \Omega$	_	144		dB
I _{CC}	Supply current	$V_O = 0$, No load		3.8		mA

NOTE 4: Typical values are based on the input offset voltage shift observed through 168 hours of operating life test at $T_A = 150^{\circ}$ C extrapolated to $T_A = 25^{\circ}$ C using the Arrhenius equation and assuming an activation energy of 0.96 eV.



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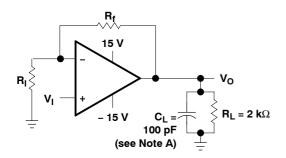
TLE20x7Y operating characteristics at specified free-air temperature, $V_{CC\,\pm}$ = $\pm 15~V$

	DADAMETED	TEST COMPLETION		TLE20x7Y		
	PARAMETER	TEST CONDITION	S	MIN TYP	MAX	UNIT
CD.	Oleverate at well-resid	$R_L = 2 k\Omega$, $C_L = 100 pF$,	TLE2027	2.8		Mora
SR	Slew rate at unity gain	See Figure 1	TLE2037	7.5		V/μs
,,	Control and insultance and the control of the contr	$R_S = 20 \Omega$, $f = 10 Hz$		3.3		nV/√ Hz
V _n	Equivalent input noise voltage (see Figure 2)	$R_S = 20 \Omega$, $f = 1 \text{ kHz}$		2.5		nv/√Hz
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz		50		nV
		f = 10 Hz		10		- A / /III
In	Equivalent input noise current	f = 1 kHz		0.8		pA/√ Hz
		$V_O = +10 \text{ V}, \ A_{VD} = 1,$ See Note 5	TLE2027	<0.002%		
THD	Total harmonic distortion	$V_O = +10 \text{ V}, \ A_{VD} = 5,$ See Note 5	TLE2037	<0.002%		
_	Heiler and heard falls (and Fig. 19.0)	D 010 0 400 E	TLE2027	13		
B ₁	Unity-gain bandwidth (see Figure 3)	$R_L = 2 k\Omega$, $C_L = 100 pF$	TLE2037	50		MHz
_		5 010	TLE2027	30		
B _{OM}	Maximum output-swing bandwidth	$R_L = 2 k\Omega$	TLE2037	80		kHz
	Phone was in all all activities Fig. 10 ()	D 010 0 100 E	TLE2027	55°		
Φm	Phase margin at unity gain (see Figure 3)	$R_L = 2 k\Omega$, $C_L = 100 pF$	TLE2037	50°		

NOTE 5: Measured distortion of the source used in the analysis was 0.002%.

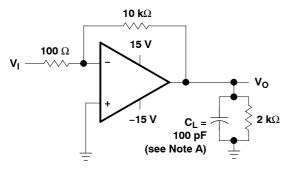
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PARAMETER MEASUREMENT INFORMATION



NOTE A: C_L includes fixture capacitance.

Figure 1. Slew-Rate Test Circuit



NOTE A: C_L includes fixture capacitance.

Figure 3. Unity-Gain Bandwidth and Phase-Margin Test Circuit (TLE2027 Only)

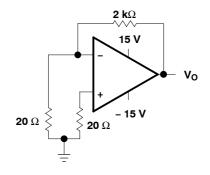
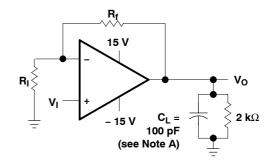


Figure 2. Noise-Voltage Test Circuit



NOTES: A. C_L includes fixture capacitance. B. For the TLE2037 and TLE2037A,

 A_{VD} must be ≥ 5 .

Figure 4. Small-Signal Pulse-Response Test Circuit



typical values

Typical values presented in this data sheet represent the median (50% point) of device parametric performance.

initial estimates of parameter distributions

In the ongoing program of improving data sheets and supplying more information to our customers, Texas Instruments has added an estimate of not only the typical values but also the spread around these values. These are in the form of distribution bars that show the 95% (upper) points and the 5% (lower) points from the characterization of the initial wafer lots of this new device type (see Figure 5). The distribution bars are shown at the points where data was actually collected. The 95% and 5% points are used instead of \pm 3 sigma since some of the distributions are not true Gaussian distributions.

The number of units tested and the number of different wafer lots used are on all of the graphs where distribution bars are shown. As noted in Figure 5, there were a total of 835 units from two wafer lots. In this case, there is a good estimate for the within-lot variability and a possibly poor estimate of the lot-to-lot variability. This is always the case on newly released products since there can only be data available from a few wafer lots.

The distribution bars are not intended to replace the minimum and maximum limits in the electrical tables. Each distribution bar represents 90% of the total units tested at a specific temperature. While 10% of the units tested fell outside any given distribution bar, this should not be interpreted to mean that the same individual devices fell outside every distribution bar.

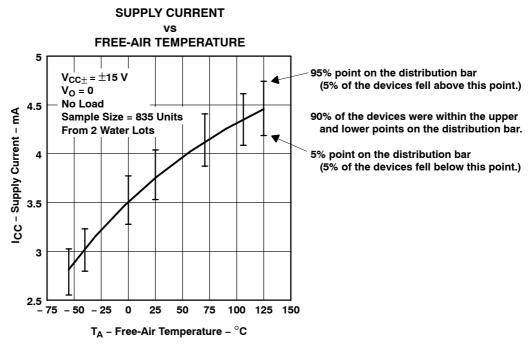


Figure 5. Sample Graph With Distribution Bars

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TYPICAL CHARACTERISTICS

Table of Graphs

			FIGURE
V_{IO}	Input offset voltage	Distribution	6, 7
ΔV_{IO}	Input offset voltage change	vs Time after power on	8, 9
I _{IO}	Input offset current	vs Free-air temperature	10
I _{IB}	Input bias current	vs Free-air temperature vs Common-mode input voltage	11 12
I _I	Input current	vs Differential input voltage	13
V _{O(PP)}	Maximum peak-to-peak output voltage	vs Frequency	14, 15
V _{OM}	Maximum (positive/negative) peak output voltage	vs Load resistance vs Free-air temperature	16, 17 18, 19
A _{VD}	Large-signal differential voltage amplification	vs Supply voltage vs Load resistance vs Frequency vs Free-air temperature	20 21 22 - 25 26
Z _O	Output impedance	vs Frequency	27
CMRR	Common-mode rejection ratio	vs Frequency	28
k _{SVR}	Supply-voltage rejection ratio	vs Frequency	29
Ios	Short-circut output current	vs Supply voltage vs Elapsed time vs Free-air temperature	30, 31 32, 33 34, 35
I _{CC}	Supply current	vs Supply voltage vs Free-air temperature	36 37
	Voltage-follower pulse response	Small signal Large signal	38, 40 39, 41
V_n	Equivalent input noise voltage	vs Frequency	42
	Noise voltage (referred to input)	Over 10-second interval	43
B ₁	Unity-gain bandwidth	vs Supply voltage vs Load capacitance	44 45
	Gain bandwidth product	vs Supply voltage vs Load capacitance	46 47
SR	Slew rate	vs Free-air temperature	48, 49
фт	Phase margin	vs Supply voltage vs Load capacitance vs Free-air temperature	50, 51 52, 53 54, 55
	Phase shift	vs Frequency	22 – 25



TYPICAL CHARACTERISTICS

DISTRIBUTION INPUT OFFSET VOLTAGE

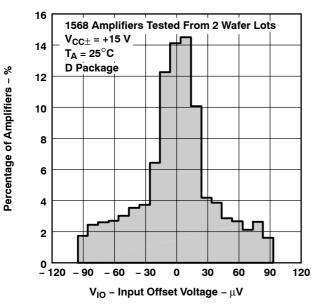
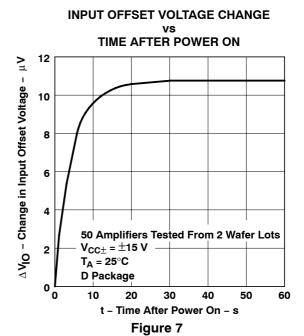
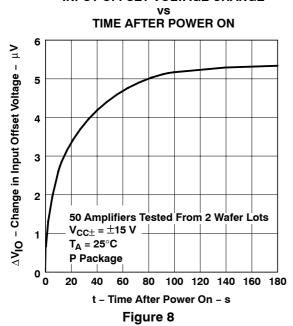


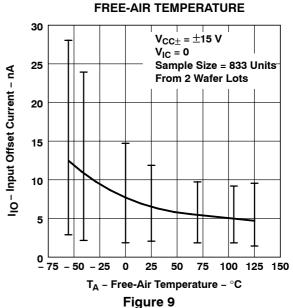
Figure 6



INPUT OFFSET VOLTAGE CHANGE



INPUT OFFSET CURRENT†
vs

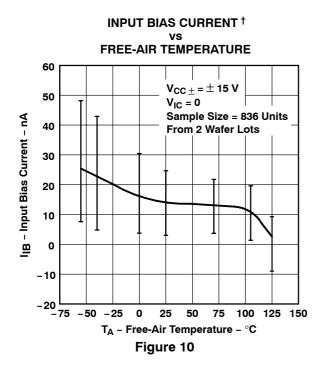


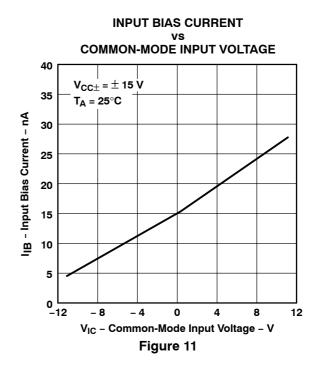
[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

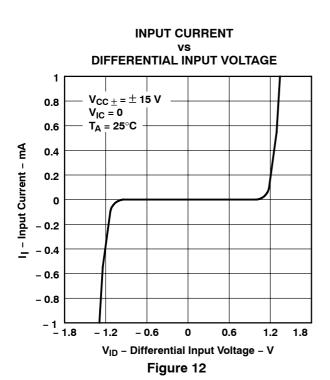


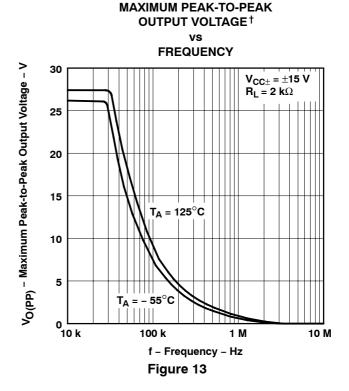
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TYPICAL CHARACTERISTICS









TLE2027

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

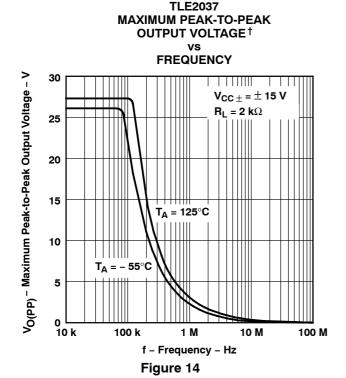


T_A = 25°C

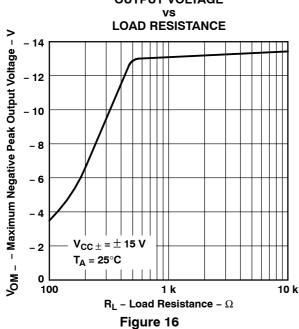
100

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TYPICAL CHARACTERISTICS







OUTPUT VOLTAGE LOAD RESISTANCE VOM + - Maximum Positive Peak Output Voltage - V 14 12 10 8 6 4 $V_{CC\,\pm}$ = \pm 15 V

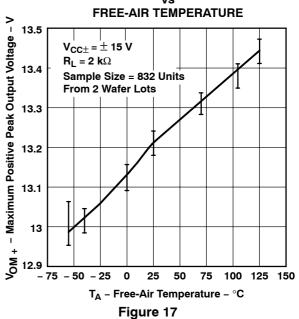
MAXIMUM POSITIVE PEAK

Figure 15 **MAXIMUM POSITIVE PEAK** OUTPUT VOLTAGE†

1 k

 $\mbox{R}_{\mbox{\scriptsize L}}$ – Load Resistance – Ω

10 k

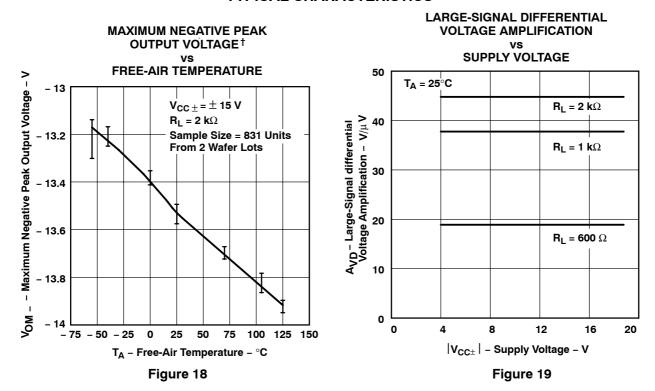


[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

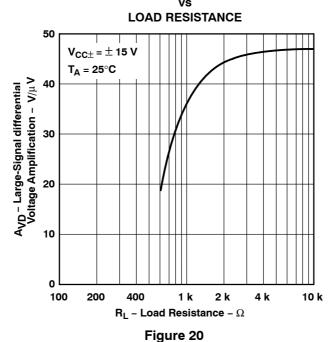


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TYPICAL CHARACTERISTICS



LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION

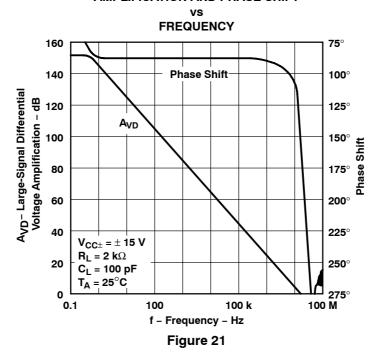


[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

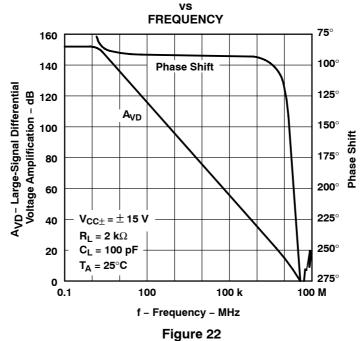


TYPICAL CHARACTERISTICS

TLE2027 LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT



TLE2037 LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

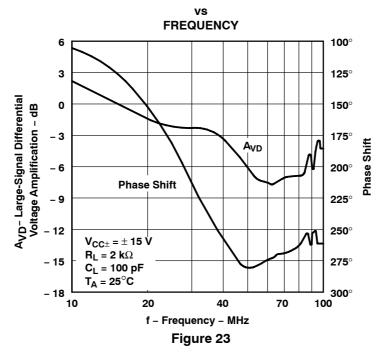




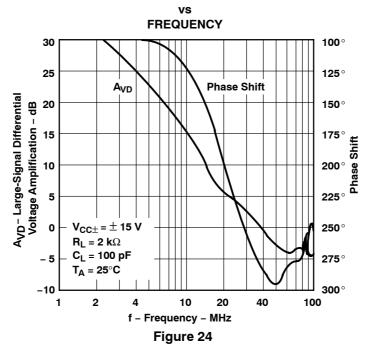
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TYPICAL CHARACTERISTICS

TLE2027 LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT



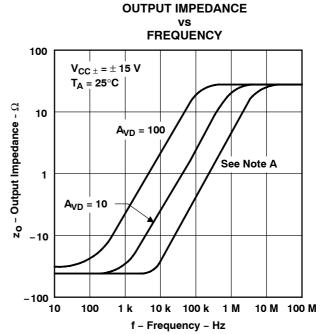
TLE2037 LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT





TYPICAL CHARACTERISTICS

LARGE-SIGNAL DIFFERENTIAL **VOLTAGE AMPLIFICATION†** vs FREE-AIR TEMPERATURE 60 $V_{CC\pm} = \pm 15 V$ $A_{VD}-$ Large-Signal differential Voltage Amplification - $V/\mu\,V$ 50 $R_L = 2 k\Omega$ $R_L = 1 k\Omega$ 30 -50 0 50 75 - 75 -25 25 100 125 150



NOTE A: For this curve, the TLE2027 is A_{VD} = 1 and the TLE2037 is A_{VD} = 5.

Figure 25

T_A - Free-Air Temperature - °C

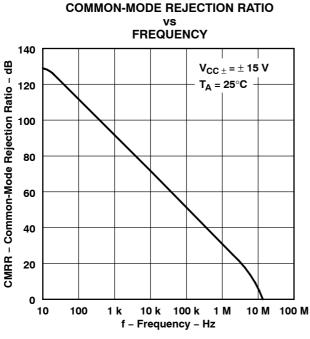


Figure 27

SUPPLY-VOLTAGE REJECTION RATIO

Figure 26

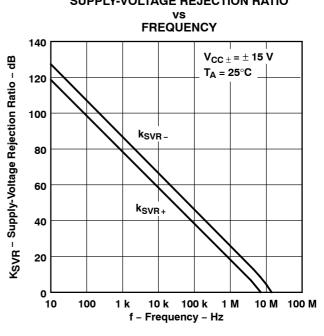


Figure 28

† Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



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TYPICAL CHARACTERISTICS

SHORT-CIRCUIT OUTPUT CURRENT **SUPPLY VOLTAGE** -42 $V_{ID} = 100 \text{ mV}$ IOS - Short-Circuit Output Current - mA $V_0 = 0$ -40 T_A = 25°C P Package -38 -36 -34 -32 -30 8 10 12 14 0 $|V_{CC^{\pm}}|$ – Supply Voltage – V

Figure 29

SHORT-CIRCUIT OUTPUT CURRENT

vs

ELAPSED TIME - 45 $V_{CC\,\pm}$ = \pm 15 V $V_{ID} = 100 \text{ mV}$ IOS - Short-Circuit Output Current - mA **V**_O = **0** T_A = 25°C - 43 P Package - 41 - 39

Figure 31

90

t - Elasped Time - s

120

150

180

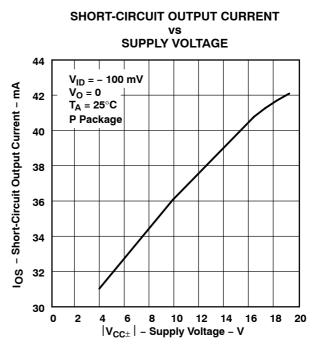


Figure 30

SHORT-CIRCUIT OUTPUT CURRENT vs **ELAPSED TIME**

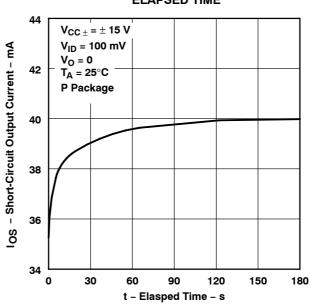


Figure 32

- 37

- 35

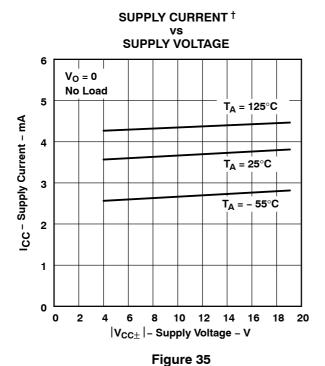
0

30

TYPICAL CHARACTERISTICS

SHORT-CIRCUIT OUTPUT CURRENT † FREE-AIR TEMPERATURE - 48 $V_{CC\,\pm}$ = \pm 15 VIOS - Short-Circuit Output Current - mA $V_{ID} = 100 \text{ mV}$ - 44 $V_0 = 0$ P Package - 40 - 36 - 32 - 28 50 - 75 - 50 25 75 100 125 T_A - Free-Air Temperature - °C

Figure 33



SHORT-CIRCUIT OUTPUT CURRENT †

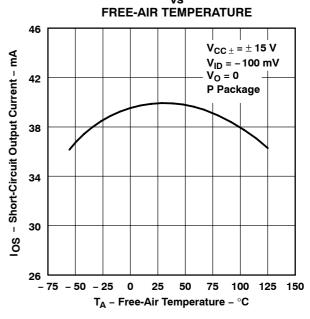


Figure 34

SUPPLY CURRENT † vs FREE-AIR TEMPERATURE

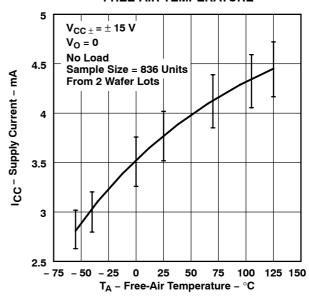


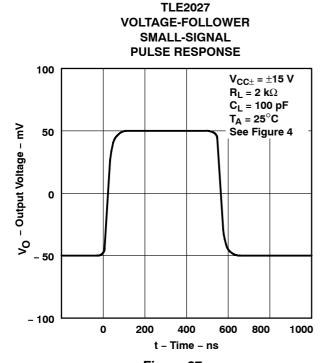
Figure 36

[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



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TYPICAL CHARACTERISTICS



VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE 15 $V_{CC\pm} = \pm 15 V$ $R_L = 2 k\Omega$ C_L = 100 pF 10 T_A = 25°C See Figure 1 V_O - Output Voltage - V 5 0 - 5 - 10 - 15

0

5

TLE2027

Figure 37

TLE2037 VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE

15

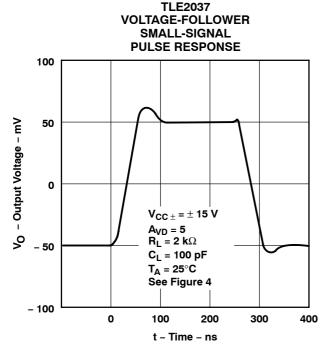
20

25

10

t - Time - μs

Figure 38



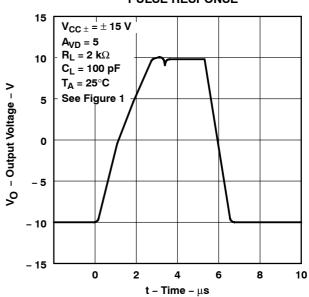


Figure 39

Figure 40



TYPICAL CHARACTERISTICS

EQUIVALENT INPUT NOISE VOLTAGE

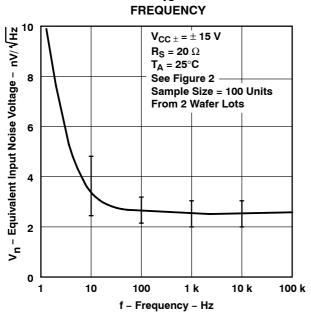


Figure 41

NOISE VOLTAGE (REFERRED TO INPUT) OVER A 10-SECOND INTERVAL

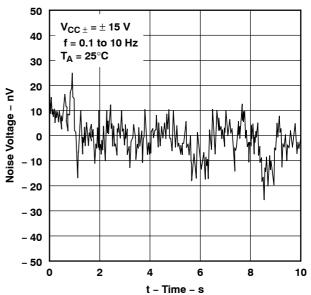
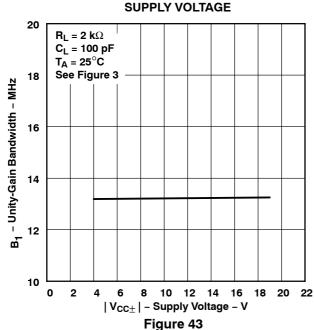
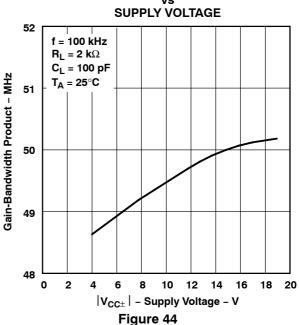


Figure 42

TLE2027 UNITY-GAIN BANDWIDTH vs

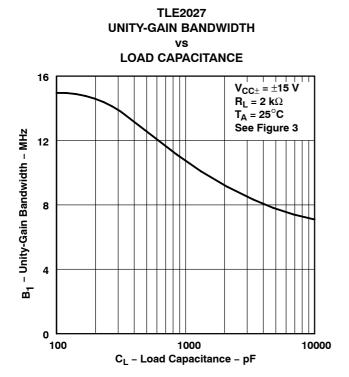


TLE2037 GAIN-BANDWIDTH PRODUCT vs



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TYPICAL CHARACTERISTICS



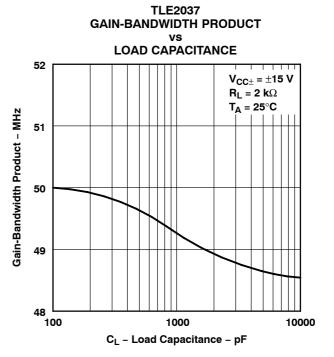
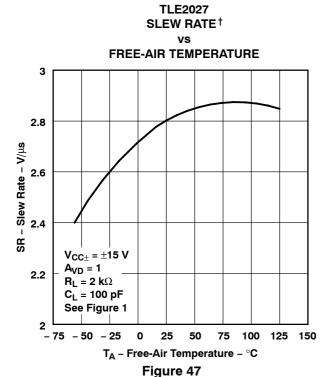


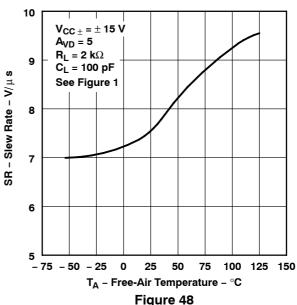
Figure 45



TLE2037

Figure 46

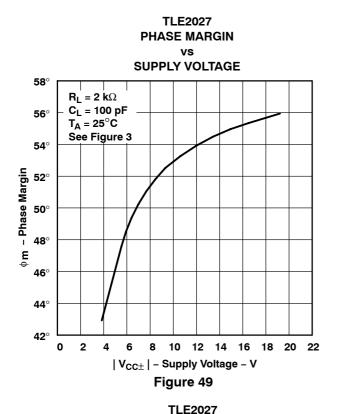


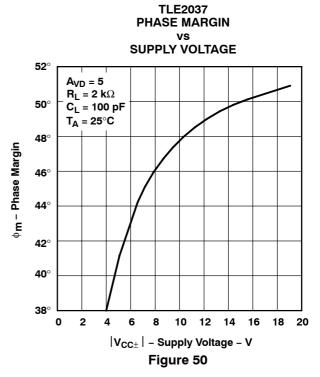


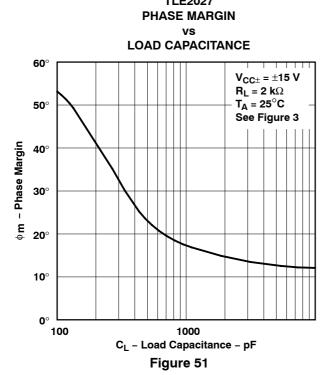
[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.

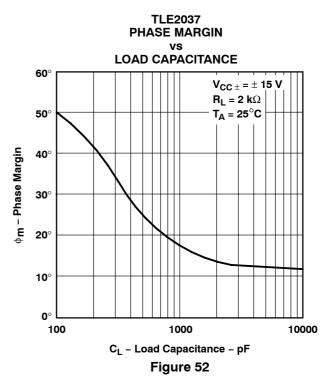


TYPICAL CHARACTERISTICS



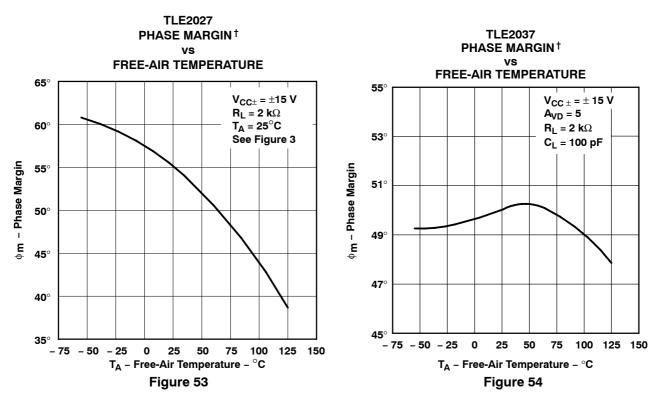






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TYPICAL CHARACTERISTICS



[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



APPLICATION INFORMATION

input offset voltage nulling

The TLE2027 and TLE2037 series offers external null pins that can be used to further reduce the input offset voltage. The circuits of Figure 55 can be connected as shown if the feature is desired. If external nulling is not needed, the null pins may be left disconnected.

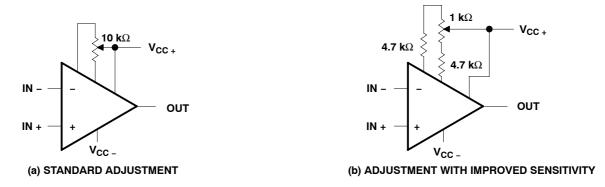


Figure 55. Input Offset Voltage Nulling Circuits

voltage-follower applications

The TLE2027 circuitry includes input-protection diodes to limit the voltage across the input transistors; however, no provision is made in the circuit to limit the current if these diodes are forward biased. This condition can occur when the device is operated in the voltage-follower configuration and driven with a fast, large-signal pulse. It is recommended that a feedback resistor be used to limit the current to a maximum of 1 mA to prevent degradation of the device. Also, this feedback resistor forms a pole with the input capacitance of the device. For feedback resistor values greater than 10 k Ω , this pole degrades the amplifier phase margin. This problem can be alleviated by adding a capacitor (20 pF to 50 pF) in parallel with the feedback resistor (see Figure 56).

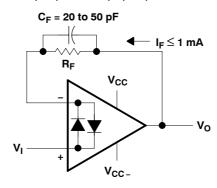


Figure 56. Voltage Follower

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APPLICATION INFORMATION

macromodel information

Macromodel information provided was derived using Microsim $Parts^{TM}$, the model generation software used with Microsim $PSpice^{TM}$. The Boyle macromodel (see Note 6) and subcircuit in Figure 57, Figure 58, and Figure 59 were generated using the TLE20x7 typical electrical and operating characteristics at 25°C. Using this information, output simulations of the following key parameters can be generated to a tolerance of 20% (in most cases):

- Maximum positive output voltage swing
- Maximum negative output voltage swing
- Slew rate
- Quiescent power dissipation
- Input bias current
- Open-loop voltage amplification

- Gain-bandwidth product
- Common-mode rejection ratio
- Phase margin
- DC output resistance
- AC output resistance
- Short-circuit output current limit

NOTE 6: G. R. Boyle, B. M. Cohn, D. O. Pederson, and J. E. Solomon, "Macromodeling of Integrated Circuit Operational Amplifiers", IEEE Journal of Solid-State Circuits, SC-9, 353 (1974).

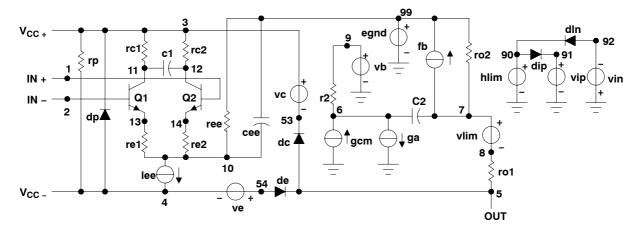


Figure 57. Boyle Macromodel

PSpice and Parts are trademarks of MicroSim Corporation.



APPLICATION INFORMATION

macromodel information (continued)

.subckt '	TLE202	7 1 2	2 3 4 5	5		q2 r2	12 6	1 9	14 100	qx .0E3
c1	11	12	4.003	BE-12		rc1	3	11	530	.5
c2	6	7	20.00			rc2	3	12	530	.5
dc	5	53	dz			re1	13	10	-39	
de	54	5	dz			re2	14	10	-39	3.2
dlp	90	91	dz			ree	10	99	3.5	71E6
dln	92	90	dx			ro1	8	5	25	
dp	4	3	dz			ro2	7	99	25	
egnd	99	0	poly(2) (3,0)	rp	3	4	8.0	13E3
(4,0) 0	5.5		`		,	vb	9	0	dc	0
` fb′	7	99	poly(5) vb vo		VC	3	53	dc	2.400
ve vlp v	ln 0 9	54.8E				ve	54	4	dc	2.100
-1E9 ⁻						vlim	7	8	dc	0
ga	6	0	11 1	.2		vlp	91	0	dc	40
2.062E-3						vln	0	92	dc	40
gcm	0	6	10 9	9		<pre>.modeldx</pre>	D(Is=	800.0	E-18)
531.3E-1	2					<pre>.modelqx</pre>	NPN(I	s=800	0.0E-	18
iee	10	4	dc 5	6.01E-6		Bf=7.000E	23)			
hlim	90	0	vlim	1K		<pre>.ends</pre>				
q 1	11	2	13 qx	2						

Figure 58. TLE2027 Macromodel Subcircuit

.subckt	TLE203	7 1	2 3 4 5	q2	12	1	14	qz
*				r2	6	9	100	.0E3
c1	11	12	4.003E-12	rc1	3	11	471	. 5
c2	6	7	7.500E-12	rc2	3	12	471	. 5
dc	5	53	dz	re1	13	10	A44	8
de	54	5	dz	re2	14	10	A44	8
dlp	90	91	dz	ree	10	99	3.5	55E6
dln	92	90	dx	ro1	8	5	25	
dp	4	3	dz	ro2	7	99	25	
egnd	99	0	poly(2) (3,0)	rp	3	4	8.0	13E3
(4	,0) 0	• 5	•5	vb	9	0	dc	0
fb	7	99	poly(5) vb vc	VC	3	53	dc	2.400
ve	vip vl	n 0	923.4E6 A800E6	ve	54	4	dc	2.100
80	0E6 800)E6 A	800E6	vlim	7	8	dc	0
ga	6	0	11 12 2.121E-3	vlp	91	0	dc	40
gcm	0	6	10 99 597.7E-12	vln	0	92	dc	40
iee	10	4	dc 56.26E-6	.model		(Is=8		
hlim	90	0	vlim 1K	.model	qxN	PN(Is	=800	.0E-18
q1	11	2	13 qx	Bf=7.0	31E3)		
				.ends				

Figure 59. TLE2037 Macromodel Subcircuit

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REVISION HISTORY

Changes from Revision B (October 2006) to Revision C	
 Changed values of V_n, V_{N(PP)}, and I_n 	1





PACKAGE OPTION ADDENDUM

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PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	n MSL Peak Temp ⁽³⁾
5962-9089601M2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
5962-9089601MPA	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type
5962-9089602MPA	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI
5962-9089603Q2A	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
5962-9089603QPA	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type
TLE2027ACD	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI
TLE2027ACP	OBSOLETE	PDIP	Р	8		TBD	Call TI	Call TI
TLE2027AID	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI
TLE2027AIP	OBSOLETE	PDIP	Р	8		TBD	Call TI	Call TI
TLE2027AMD	ACTIVE	SOIC	D	8	75	TBD	CU NIPDAU	Level-1-220C-UNLIM
TLE2027AMDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2027AMFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
TLE2027AMJG	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type
TLE2027AMJGB	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type
TLE2027CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2027CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2027CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2027CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2027CP	OBSOLETE	PDIP	Р	8		TBD	Call TI	Call TI
TLE2027ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2027IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2027IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2027IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2027IP	OBSOLETE	PDIP	Р	8		TBD	Call TI	Call TI
TLE2027MD	ACTIVE	SOIC	D	8	75	TBD	CU NIPDAU	Level-1-220C-UNLIM
TLE2027MDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2027MFKB	ACTIVE	LCCC	FK	20	1	TBD	POST-PLATE	N / A for Pkg Type
TLE2027MJG	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type
TLE2027MJGB	ACTIVE	CDIP	JG	8	1	TBD	A42	N / A for Pkg Type
TLE2037ACD	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI
TLE2037ACP	OBSOLETE	PDIP	Р	8		TBD	Call TI	Call TI
TLE2037AID	OBSOLETE	SOIC	D	8		TBD	Call TI	Call TI
TLE2037AIP	OBSOLETE	PDIP	Р	8		TBD	Call TI	Call TI
TLE2037AMD	ACTIVE	SOIC	D	8	75	TBD	CU NIPDAU	Level-1-220C-UNLIM
TLE2037AMDG4	ACTIVE	SOIC	D	8	75	Green (RoHS &	CU NIPDAU	Level-1-260C-UNLIM



PACKAGE OPTION ADDENDUM

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Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Packag Qty	e Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
						no Sb/Br)		
TLE2037AMJGB	OBSOLETE	CDIP	JG	8		TBD	Call TI	Call TI
TLE2037CD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2037CDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2037CDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2037CDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2037CP	OBSOLETE	PDIP	Р	8		TBD	Call TI	Call TI
TLE2037ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2037IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2037IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2037IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2037IP	OBSOLETE	PDIP	Р	8		TBD	Call TI	Call TI
TLE2037MD	ACTIVE	SOIC	D	8	75	TBD	CU NIPDAU	Level-1-220C-UNLIM
TLE2037MDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
TLE2037MFKB	OBSOLETE	LCCC	FK	20		TBD	Call TI	Call TI
TLE2037MJGB	OBSOLETE	CDIP	JG	8	•	TBD	Call TI	Call TI

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF TLE2027, TLE2027A, TLE2027AM, TLE2027M, TLE2037, TLE2037A:

• Automotive: TLE2037-Q1, TLE2037A-Q1

• Enhanced Product: TLE2027-EP

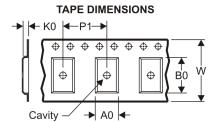
NOTE: Qualified Version Definitions:

- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product Supports Defense, Aerospace and Medical Applications

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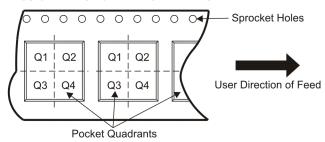
TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

All difficultions are norminal												
Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLE2027CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLE2027IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLE2037CDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLE2037IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



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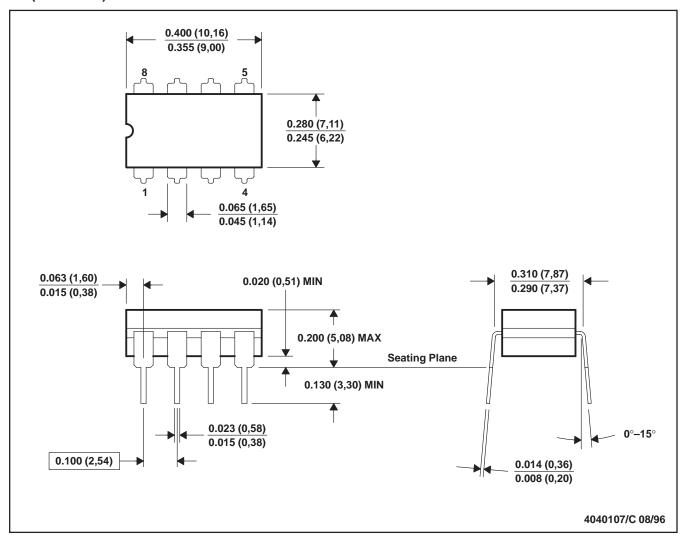


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLE2027CDR	SOIC	D	8	2500	340.5	338.1	20.6
TLE2027IDR	SOIC	D	8	2500	340.5	338.1	20.6
TLE2037CDR	SOIC	D	8	2500	340.5	338.1	20.6
TLE2037IDR	SOIC	D	8	2500	340.5	338.1	20.6

JG (R-GDIP-T8)

CERAMIC DUAL-IN-LINE



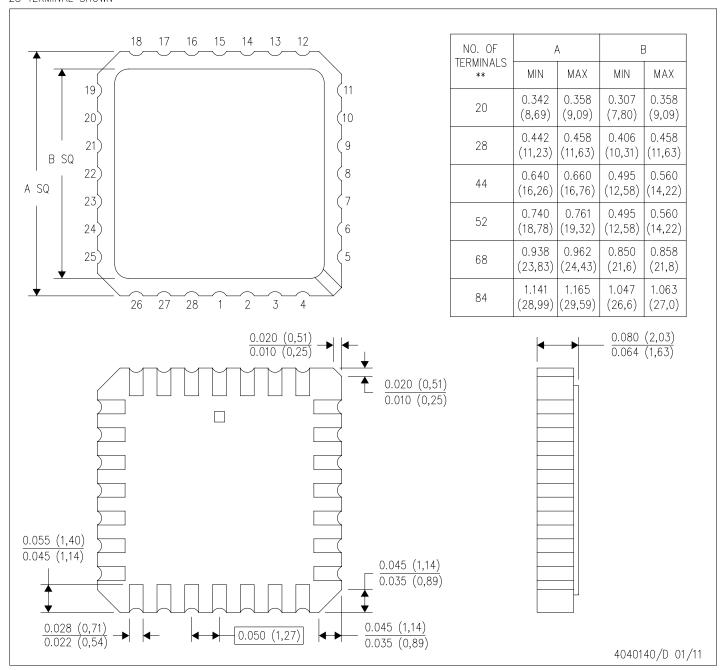
NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification.
- E. Falls within MIL STD 1835 GDIP1-T8

FK (S-CQCC-N**)

LEADLESS CERAMIC CHIP CARRIER

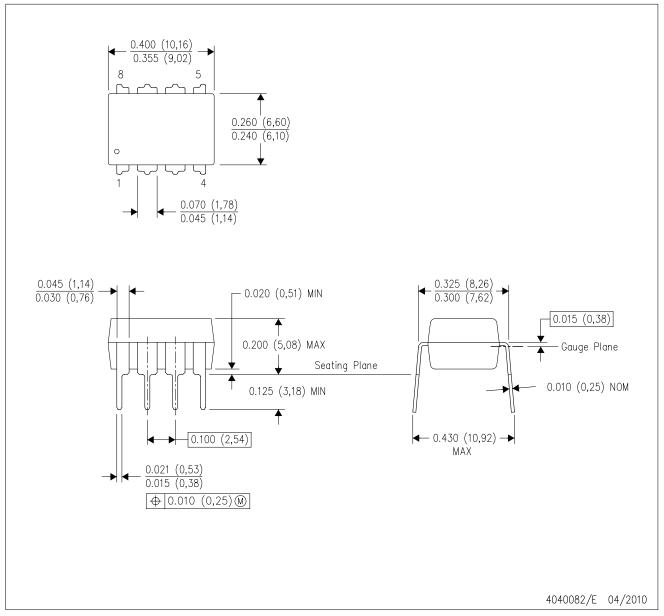
28 TERMINAL SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a metal lid.
- D. Falls within JEDEC MS-004

P (R-PDIP-T8)

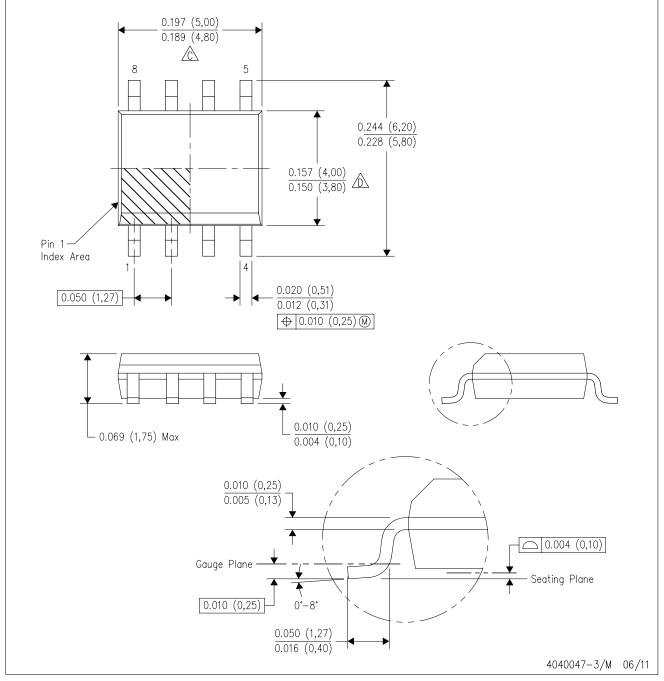
PLASTIC DUAL-IN-LINE PACKAGE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 variation BA.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE

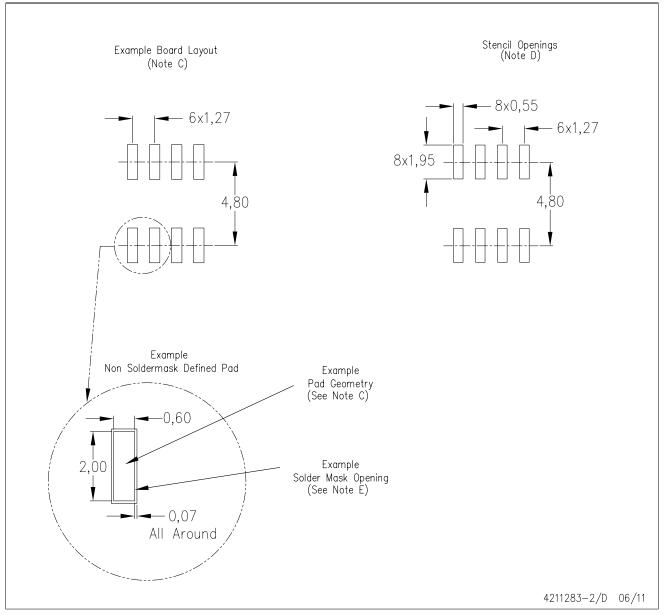


- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AA.



D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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DLP® Products	www.dlp.com	Energy and Lighting	www.ti.com/energy
DSP	dsp.ti.com	Industrial	www.ti.com/industrial
Clocks and Timers	www.ti.com/clocks	Medical	www.ti.com/medical
Interface	interface.ti.com	Security	www.ti.com/security
Logic	logic.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Power Mgmt	power.ti.com	Transportation and Automotive	www.ti.com/automotive
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video
RFID	www.ti-rfid.com	Wireless	www.ti.com/wireless-apps
RF/IF and ZigBee® Solutions	www.ti.com/lprf		
	Audio Amplifiers Data Converters DLP® Products DSP Clocks and Timers Interface Logic Power Mgmt Microcontrollers RFID	Audio www.ti.com/audio Amplifiers amplifier.ti.com Data Converters dataconverter.ti.com DLP® Products www.dlp.com DSP dsp.ti.com Clocks and Timers www.ti.com/clocks Interface interface.ti.com Logic logic.ti.com Power Mgmt power.ti.com Microcontrollers microcontroller.ti.com RFID www.ti.rid.com	Audio www.ti.com/audio Communications and Telecom Amplifiers amplifier.ti.com Computers and Peripherals Data Converters dataconverter.ti.com Consumer Electronics DLP® Products www.dlp.com Energy and Lighting DSP dsp.ti.com Industrial Clocks and Timers www.ti.com/clocks Medical Interface interface.ti.com Security Logic logic.ti.com Space, Avionics and Defense Power Mgmt power.ti.com Transportation and Automotive Microcontrollers microcontroller.ti.com Wireless Wireless

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